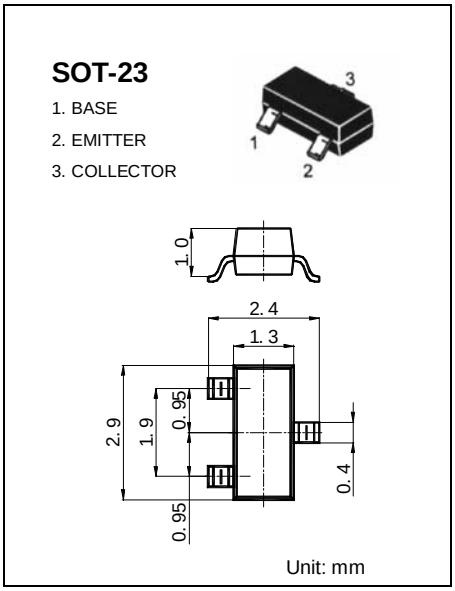
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

MMBT2222LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.3 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 10μA, I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 10mA, I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			0.01	μA
Collector cut-off current	I_{CEO}	V_{CE}=10V, I_B=0			0.1	μA
Collector cut-off current	I_{EBO}	V_{EB}=3V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10V, I_C= 0.1mA	35			
	$h_{FE(2)}$	V_{CE}=10V, I_C= 150mA	100		300	
	$h_{FE(3)}$	V_{CE}=10V, I_C= 500mA	30			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B=50mA			1	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500 mA, I_B=50mA			2	V
Transition frequency	f_T	V_{CE}= 20V, I_C=20mA f=100MHz	250			MHz

Marking	**M1B**